HALOGEN

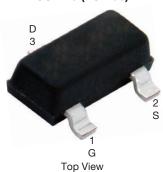
FREE



Vishay Siliconix

N-Channel 60 V (D-S) MOSFET

SOT-23 (TO-236)



Marking code: 7K

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	2			
Q _g typ. (nC)	0.4			
I _D (A)	0.3			
Configuration	Single			

FEATURES

Low on-resistance: 2 Ω
Low threshold: 2 V (typ.)

Low input capacitance: 25 pFFast switching speed: 25 ns

Low input and output leakage

• TrenchFET® power MOSFET

• 2000 V ESD protection

 Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

Note

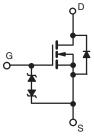
* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

BENEFITS

- · Low offset voltage
- · Low voltage operation
- · Easily driven without buffer
- · High speed circuits
- · Low error voltage

APPLICATIONS

- Direct logic-level interface: TTL/CMOS
- Drivers: relays, solenoids, lamps, hammers, display, memories, transistors, etc.
- · Battery operated systems
- Solid state relays



N-Channel MOSFET

ORDERING INFORMATION				
Package	SOT-23			
Lead (Pb)-free	2N7002K-T1-E3			
Lead (Pb)-free and halogen-free	2N7002K-T1-GE3			

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V_{DS}	60	V		
Gate-source voltage			± 20	V		
Continuous drain current (T _{.J} = 150 °C) ^b	T _A = 25 °C	- I _D	0.3	А		
Continuous drain current (1) = 150 C) 5	T _A = 100 °C		0.19			
Pulsed drain current ^a		I_{DM}	0.8			
Power dissipation ^b	T _A = 25 °C	В	0.35	W		
Fower dissipation •	T _A = 100 °C	- P _D	0.14			
Maximum junction-to-ambient ^b		R_{thJA}	350	°C/W		
Operating junction and storage temperature range		T _{J,} T _{stg}	-55 to +150	°C		

Notes

- a. Pulse width limited by maximum junction temperature
- b. Surface mounted on FR4 board



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP. a	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 10 \mu\text{A}$	60	-	-	V	
Gate-threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	-	2.5	V	
Gate-body leakage		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 10	μА	
		$V_{DS} = 0 V, V_{GS} = \pm 15 V$	=.	-	1		
	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$	-	-	± 150		
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$	-	-	± 1000	nA	
		$V_{DS} = 0 V, V_{GS} = \pm 5 V$	=.	-	± 100		
Zero gate voltage drain current		V _{DS} = 60 V, V _{GS} = 0 V	-	-	1		
	I _{DSS}	V_{DS} = 60 V, V_{GS} = 0 V, T_J = 125 °C	=.	-	500	μA	
On-state drain current ^b		$V_{GS} = 10 \text{ V}, V_{DS} = 7.5 \text{ V}$	800	-	-	mA	
	I _{D(on)}	$V_{GS} = 4.5 \text{ V}, V_{DS} = 10 \text{ V}$	500	-	-		
Drain-source on-resistance ^b	В	$V_{GS} = 10 \text{ V}, I_D = 500 \text{ mA}$	=.	-	2	Ω	
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 200 \text{ mA}$	-	-	4		
Forward transconductance b	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 200 \text{ mA}$ 100		-	-	mS	
Diode forward voltage	V _{SD}	$I_S = 200 \text{ mA}, V_{GS} = 0 \text{ V}$	-	-	1.3	V	
Dynamic ^{a, b}							
Total gate charge	Qg	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}$ $I_D \cong 250 \text{ mA}$	-	0.4	0.6	nC	
Input capacitance	C _{iss}		-	30	-		
Output capacitance	C _{oss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$ f = 1 MHz	-	6	-	pF	
Reverse transfer capacitance	C _{rss}	1 – 1 141112	-	2.5	-		
Switching ^{a, c}			•				
Turn-on time	t _{d(on)}	$V_{DD} = 30 \text{ V}, R_{I} = 150 \Omega$	-	-	25		
Turn-off time	t _{d(off)}	$I_D \cong 200 \text{ mA}, V_{GEN} = 10 \text{ V}, R_g = 10 \Omega$	-	-	35	ns	

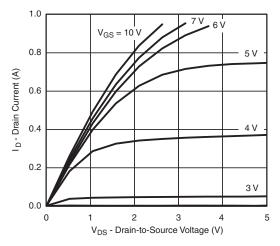
Notes

- a. For DESIGN AID ONLY, not subject to production testing
- b. Pulse test: pulse width \leq 300 μs duty cycle \leq 2 %
- c. Switching time is essentially independent of operating temperature

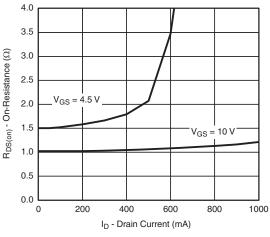
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



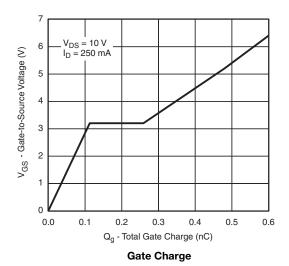
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

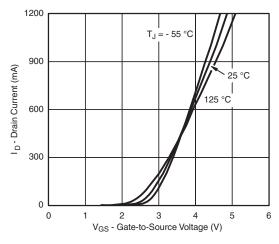


Output Characteristics

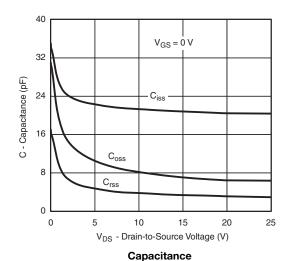


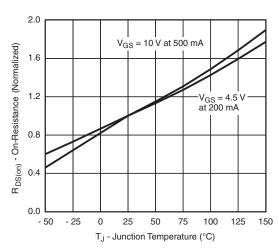
On-Resistance vs. Drain Current





Transfer Characteristics

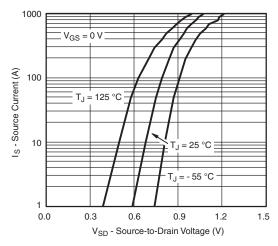




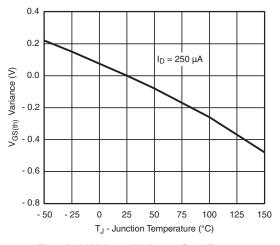
On-Resistance vs. Junction Temperature



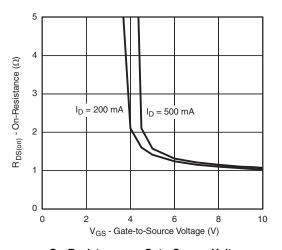
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



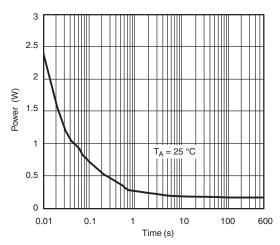
Source-Drain Diode Forward Voltage



Threshold Voltage Variance Over Temperature



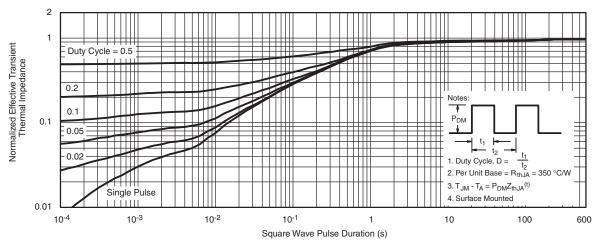
On-Resistance vs. Gate-Source Voltage



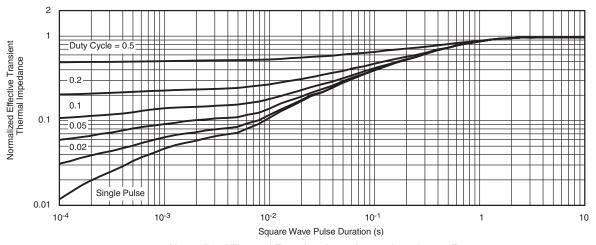
Single Pulse Power, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

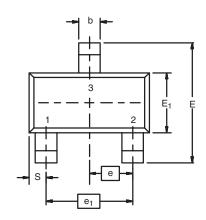


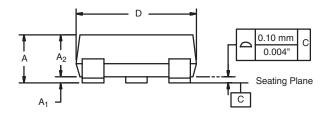
Normalized Thermal Transient Impedance, Junction-to-Foot

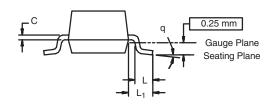
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SOT-23 (TO-236): 3-LEAD







Dim	MILLIMETERS		INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.074	8 Ref	
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
FCN: S-03946-Rev K 09-	lul-01	•			

ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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